506482154 02/02/2021

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
ZHENG LONG CHEN	08/07/2020

RECEIVING PARTY DATA

Name:	TAIWAN SEMICONDUCTOR MANUFACTURING COMPANY, LTD.	
Street Address:	8, LI-HSIN RD. 6, HSINCHU SCIENCE PARK	
City:	HSINCHU	
State/Country:	TAIWAN	
Postal Code:	300-78	
Name:	TSMC CHINA COMPANY, LIMITED	
Street Address:	4000, WEN XIANG RD.	
City:	SONGJIANG	
State/Country:	CHINA	

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	17165165

CORRESPONDENCE DATA

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using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

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ATTORNEY DOCKET NUMBER:	T5057-1522	
NAME OF SUBMITTER:	RANDY A. NORANBROCK	
SIGNATURE:	/Randy A. Noranbrock/	
DATE SIGNED:	02/02/2021	

Total Attachments: 1

PATENT REEL: 055112 FRAME: 0789

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PATENT REEL: 055112 FRAME: 0790

ASSIGNMENT

In consideration of the premises and other good and valuable consideration in hand paid, the receipt and sufficiency of which is hereby acknowledged, the undersigned,

1) Zheng Long CHEN

who has made a certain new and useful invention, hereby sells, assigns and transfers unto TAIWAN SEMICONDUCTOR MANUFACTURING COMPANY, LTD., having a place of business at No. 8, Li-Hsin Rd. VI, Hsinchu Science Park, Hsinchu 300, Taiwan R.O.C. and

TSMC CHINA COMPANY, LIMITED, having a place of business at 4000. Wen Xians Rd., Songitang, Shanghai, CHINA its successors and assigns (hereinafter designated "ASSIGNEE") the entire right, title and interest for the United States of America as defined in 35 U.S.C. 100 in the invention entitled

LATERALLY DIFFUSED MOSFET AND METHOD OF FABRICATING THE SAME

(a) for which an application for United States Letters Patent was filed on ______, and identified by United States Patent Application No. ______; or

(b) for which an application for United States Letters Patent was executed on ______, and all dentified by United States Letters Patent was executed on ______, and all United States Letters Patent which may be granted therefore and any and all extensions, divisions, reissues, continuations, or

AND the undersigned hereby agrees to transfer a like interest, and to render all necessary assistance in making application for and obtaining original, divisional, reissued or extended Letters Patent of the United States, upon request of the said ASSIGNEE, its successors, assigns and legal representatives, and without further remuneration, in and to any improvements, and applications for patent based thereon, growing out of or related to the said invention; and to execute any papers by the said ASSIGNEE, its successors, assigns and legal representatives, deemed essential to ASSIGNEE's full protection and title in and to

continuations-in-part thereof, and the right to all benefits under the International Convention for the Protection of Industrial Property to the said ASSIGNEE, for its interest as ASSIGNEE, its successors, assigns and legal representatives; the undersigned

agrees that the attorneys of record in said application shall hereafter act on behalf of said ASSIGNEE;

SIGNED on the date indicated aside my signature:

the invention hereby transferred.

1) Zheng Long CHEN
Name: Zheng Long CHEN

2020/8/7

Date

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